

Description

The TSV63x and TSV63xA series of dual and quad operational amplifiers offers low voltage operation and rail-to-rail input and output.

This family features an excellent speed/power consumption ratio, offering an 880 kHz gain-bandwidth product while consuming only 60 µA at 5 V supply voltage.

These features make the TSV63x and TSV63xA family ideal for sensor interfaces, battery-supplied and portable applications, and active filtering.

Applications

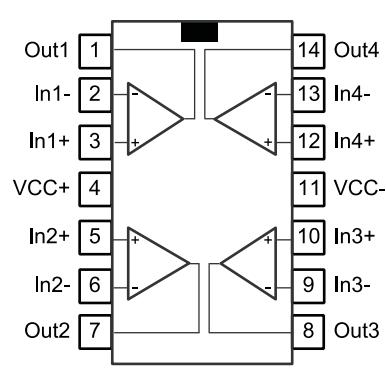
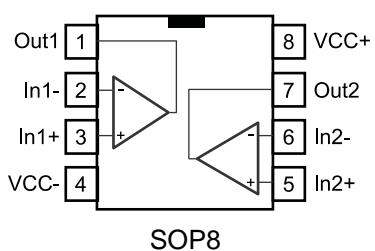
- Battery-powered applications
- Portable devices
- Signal conditioning
- Active filtering
- Medical instrumentation

Features

- Rail-to-rail input and output
- Low power consumption: 60 µA typ at 5 V
- Low supply voltage: 1.5 V - 5.5 V
- Gain bandwidth product: 880 kHz typ
- Unity gain stable on 100 pF capacitor
- Low power shutdown mode: 5 nA typ
- Low offset voltage: 800 µV max (A version)
- Low input bias current: 1 pA typ
- EMI hardened op amps
- Automotive qualification

Package pin connections

Figure 1: Pin connections for each package (top view)



Absolute maximum ratings and operating conditions

Table 2: Absolute maximum ratings (AMR)

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	6	V
V_{id}	Differential input voltage	$\pm V_{CC}$	
V_{IN}	Input voltage	$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$	
I_{IN}	Input current	10	mA
SHDN SHDN	Shutdown voltage	$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$	V
T_{STG}	Storage temperature	-65 to 150	°C
R_{thja}	Thermal resistance junction to ambient	SOP8	125
		TSSOP14	100
T_j	Maximum junction temperature	150	°C
ESD	HBM: human body model	4000	V
	MM: machine model	300	
	CDM: charged device model	1500	
	Latch-up immunity	200	mA

Notes:

- (1) All voltage values, except the differential voltage are with respect to the network ground terminal.
- (2) Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
- (3) $V_{CC} - V_{IN}$ must not exceed 6 V, V_{IN} must not exceed 6 V.
- (4) Input current must be limited by a resistor in series with the inputs
- (5) R_{th} are typical values
- (6) Short-circuits can cause excessive heating and destructive dissipation
- (7) Human body model: 100 pF discharged through a 1.5 k Ω resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- (8) Machine model: a 200 pF cap is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating
- (9) Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to the ground.

Table 3: Operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	1.5 to 5.5	V
V_{ICM}	Common-mode input voltage range	$(V_{CC-}) - 0.1$ to $(V_{CC+}) + 0.1$	
T_{oper}	Operating free-air temperature range	-40 to 125	°C

Electrical characteristics

Table 4: Electrical characteristics at $V_{CC+} = 1.8$ V with $V_{CC-} = 0$ V, $V_{ICM} = V_{CC}/2$, $T_{amb} = 25^\circ$ C, and R_L connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{IO}	Offset voltage	$TSV63x$			3	mV
		$TSV63xA$			0.8	
		$T_{min} < T_{op} < T_{max}$ - $TSV63x$			4.5	
		$T_{min} < T_{op} < T_{max}$ - $TSV63xA$			2	
				2		
$\Delta V_{IO}/\Delta T$	Input offset voltage drift					μ V/°C
I_{IO}	Input offset current	$(V_{out} = V_{CC}/2)$		1	10	pA
		$T_{min} < T_{op} < T_{max}$		1	100	
I_{IB}	Input bias current	$(V_{out} = V_{CC}/2)$		1	10	
		$T_{min} < T_{op} < T_{max}$		1	100	
CMR	Common mode rejection ratio $20 \log (\Delta V_{IO}/\Delta V_{IO})$	0 V to 1.8 V, $V_{out} = 0.9$ V	53	74		dB
		$T_{min} < T_{op} < T_{max}$	51			
A_{VD}	Large signal voltage gain	$R_L = 10$ k Ω , $V_{out} = 0.5$ V to 1.3 V	85	95		
		$T_{min} < T_{op} < T_{max}$	80			
V_{OH}	High level output voltage, ($V_{OH} = V_{CC} - V_{out}$)	$R_L = 10$ k Ω		5	35	mV
		$T_{min} < T_{op} < T_{max}$			50	
V_{OL}	Low level output voltage	$R_L = 10$ k Ω		4	35	
		$T_{min} < T_{op} < T_{max}$			50	
I_{OUT}	I_{sink}	$V_o = 1.8$ V	6	12		mA
		$T_{min} < T_{op} < T_{max}$	4			
	I_{source}	$V_o = 0$ V	6	10		
		$T_{min} < T_{op} < T_{max}$	4			
I_{CC}	Supply current (per channel)	No load, $V_{out} = V_{CC}/2$	40	50	60	μ A
		$T_{min} < T_{op} < T_{max}$			62	
AC performance						
GBP	Gain bandwidth product	$R_L = 2$ k Ω , $C_L = 100$ pF, $f = 100$ kHz	700	790		kHz
ϕ_m	Phase margin	$R_L = 2$ k Ω , $C_L = 100$ pF		45		Degrees
G_m	Gain margin	$R_L = 2$ k Ω , $C_L = 100$ pF		13		dB
SR	Slew rate	$R_L = 2$ k Ω , $C_L = 100$ pF, $A_v = 1$	0.2	0.27		V/ μ s
e_n	Equivalent input noise voltage	$f = 1$ kHz		60		n V/ \sqrt{Hz}
		$f = 10$ kHz		33		

Table 5: Shutdown characteristics VCC = 1.8 V

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
I _{CC}	Supply current in shutdown mode (all channels)	SHDN = V _{CC-}		2.5	50	nA
		T _{min} < T _{op} < 85°C			200	
		T _{min} < T _{op} < 125°C			1.5	μA
t _{on}	Amplifier turn-on time	R _L = 2 kΩ, V _{out} = (V _{CC-}) to (V _{CC-}) + 0.2 V		200		ns
t _{off}	Amplifier turn-off time	R _L = 2 kΩ, V _{out} = (V _{CC+}) - 0.5 V to (V _{CC+}) - 0.7 V		20		
V _{IH}	SHDN logic high		1.35			V
V _{IL}	SHDN logic low				0.6	
I _{IH}	SHDN current high	SHDN = V _{CC+}		10		pA
I _{IL}	SHDN current low	SHDN = V _{CC-}		10		
I _{OLeak}	Output leakage in shutdown mode	SHDN = V _{CC-}		50		nA
		T _{min} < T _{op} < 125°C		1		

Table 6: VCC+ = 3.3 V, VCC- = 0 V, Vicm = VCC/2, Tamb = 25° C, RL connected to VCC/2 (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V _{io}	Offset voltage	TSV63x			3	mV
		TSV63xA			0.8	
		T _{min} < T _{op} < T _{max} - TSV63x			4.5	
		T _{min} < T _{op} < T _{max} - TSV63xA			2	
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		μ V/°C
I _{io}	Input offset current	V _{out} = V _{CC} /2		1	10 ⁽¹⁾	pA
		T _{min} < T _{op} < T _{max}		1	100	
I _{ib}	Input bias current	V _{out} = V _{CC} /2		1	10 ⁽¹⁾	
		T _{min} < T _{op} < T _{max}		1	100	
CMR	Common mode rejection ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$)	0 V to 3.3 V, V _{out} = 1.65 V	57	79		dB
		T _{min} < T _{op} < T _{max}	53			
A _{vd}	Large signal voltage gain	R _L = 10 k Ω , V _{out} = 0.5 V to 2.8 V	88	98		
		T _{min} < T _{op} < T _{max}	83			
V _{OH}	High level output voltage, (V _{OH} = V _{CC} - V _{out})	R _L = 10 k Ω		5	35	mV
		T _{min} < T _{op} < T _{max}			50	
V _{OL}	Low level output voltage	R _L = 10 k Ω		4	35	
		T _{min} < T _{op} < T _{max}			50	
I _{out}	I _{sink}	V _o = 3.3 V	23	45		mA
		T _{min} < T _{op} < T _{max}	20			
	I _{source}	V _o = 0 V	23	38		
		T _{min} < T _{op} < T _{max}	20			
I _{cc}	Supply current, (per channel)	No load, V _{out} = 1.75 V	43	55	64	μ A
		T _{min} < T _{op} < T _{max}			66	
AC performance						
GBP	Gain bandwidth product	R _L = 2 k Ω , C _L = 100 pF, f = 100 kHz	710	860		kHz
ϕ_m	Phase margin	R _L = 2 k Ω , C _L = 100 pF		46		Degrees
G _m	Gain margin	R _L = 2 k Ω , C _L = 100 pF		13		dB
SR	Slew rate	R _L = 2 k Ω , C _L = 100 pF, A _V = 1	0.22	0.29		V/ μ s

Table 7: Electrical characteristics at VCC+ = 5 V with VCC- = 0 V, Vicm = VCC/2, Tamb = 25° C, and RL connected to VCC/2 (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V _{io}	Offset voltages	TSV63x			3	mV
		TSV63xA			0.8	
		T _{min} < T _{op} < T _{max} - TSV63x			4.5	
		T _{min} < T _{op} < T _{max} - TSV63xA			2	
ΔV _{io} /ΔT	Input offset voltage drift			2		μV/°C
I _{io}	Input offset current	(V _{out} = V _{CC} /2)		1	10 ⁽¹⁾	pA
		T _{min} < T _{op} < T _{max}		1	100	
I _{ib}	Input bias current	(V _{out} = V _{CC} /2)		1	10 ⁽¹⁾	
		T _{min} < T _{op} < T _{max}		1	100	
CMR	Common mode rejection ratio 20 log (ΔV _{ic} /ΔV _{io})	0 V to 5 V, V _{out} = 2.5 V	60	80		dB
		T _{min} < T _{op} < T _{max}	55			
SVR	Supply voltage rejection ratio 20 log (ΔV _{CC} /ΔV _{io})	V _{CC} = 1.8 to 5 V	75	102		
		T _{min} < T _{op} < T _{max}	73			
A _{vd}	Large signal voltage gain	R _L = 10 kΩ, V _{out} = 0.5 V to 4.5 V	89	98		dB
		T _{min} < T _{op} < T _{max}	84			
EMIRR	EMI rejection ratio, EMIRR = -20 log (V _{RFpeak} /ΔV _{io})	V _{RF} = 100 mV _{rms} , f = 400 MHz		61		
		V _{RF} = 100 mV _{rms} , f = 900 MHz		85		
		V _{RF} = 100 mV _{rms} , f = 1800 MHz		92		
		V _{RF} = 100 mV _{rms} , f = 2400 MHz		83		
V _{OH}	High level output voltage, (V _{OH} = V _{CC} - V _{out})	R _L = 10 kΩ		7	35	mV
		T _{min} < T _{op} < T _{max}			50	
V _{OL}	Low level output voltage	R _L = 10 kΩ		6	35	
		T _{min} < T _{op} < T _{max}			50	
I _{out}	I _{sink}	V _o = 5 V	40	69		mA
		T _{min} < T _{op} < T _{max}	35			
	I _{source}	V _o = 0 V	40	74		
		T _{min} < T _{op} < T _{max}	35			
I _{cc}	Supply current, (per channel)	No load, V _{out} = V _{CC} /2	50	60	69	μA
		T _{min} < T _{op} < T _{max}			72	
AC performance						
GBP	Gain bandwidth product	R _L = 2 kΩ, C _L = 100 pF, f = 100 kHz	730	880		kHz
F _u	Unity gain frequency	R _L = 2 kΩ, C _L = 100 pF		830		
φm	Phase margin	R _L = 2 kΩ, C _L = 100 pF		48		
						Degrees

Electrical characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
G_m	Gain margin	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}$		13		dB
SR	Slew rate	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}, A_v = 1$	0.25	0.34		V/ μ s
e_n	Equivalent input noise voltage	$f = 1 \text{ kHz}$		60		nV/ $\sqrt{\text{Hz}}$
		$f = 10 \text{ kHz}$		33		
THD+ e_n	Total harmonic distortion + noise	$V_{CC} = 5\text{V}, f = 1 \text{ kHz}, A_v = 1, R_L = 100 \text{ k}\Omega, V_{icm} = V_{CC}/2, V_{out} = 2\text{Vpp}$		0.002		%

Notes:

(1) Guaranteed by design

Table 8: Shutdown characteristics at $V_{CC} = 5 \text{ V}$

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
I_{CC}	Supply current in shutdown mode (all channels)	$\overline{SHDN} = V_{CC-}$		5	50	nA
		$T_{min} < T_{op} < 85^\circ \text{C}$			200	
		$T_{min} < T_{op} < 125^\circ \text{C}$			1.5	µA
t_{on}	Amplifier turn-on time	$R_L = 2 \text{ k}\Omega, V_{out} = (V_{CC-}) \text{ to } (V_{CC-}) + 0.2 \text{ V}$		200		ns
t_{off}	Amplifier turn-off time	$R_L = 2 \text{ k}\Omega, V_{out} = (V_{CC+}) - 0.5 \text{ V} \text{ to } (V_{CC+}) - 0.7 \text{ V}$		20		
V_{IH}	\overline{SHDN} logic high		2			V
V_{IL}	\overline{SHDN} logic low				0.8	
I_{IH}	\overline{SHDN} current high	$\overline{SHDN} = V_{CC+}$		10		pA
I_{IL}	\overline{SHDN} current low	$\overline{SHDN} = V_{CC-}$		10		
I_{OLeak}	Output leakage in shutdown mode	$\overline{SHDN} = V_{CC-}$		50		nA
		$T_{min} < T_{op} < 125^\circ \text{C}$		1		

Figure 2: Supply current vs. supply voltage at $V_{ICM} = V_{CC}/2$

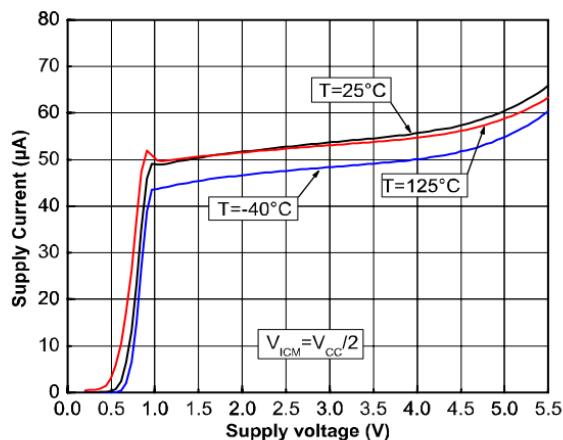


Figure 3: Output current vs. output voltage at $V_{CC} = 1.5\text{ V}$

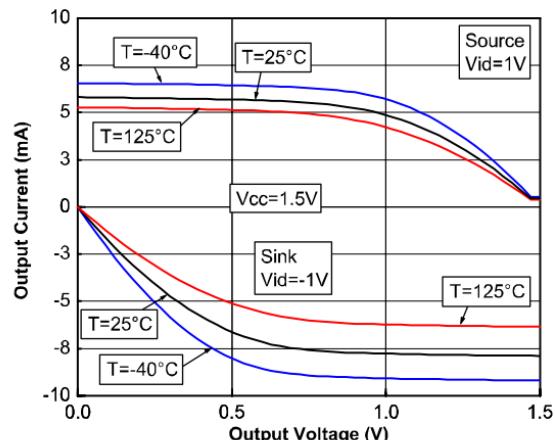


Figure 4: Output current vs. output voltage at $V_{CC} = 5\text{ V}$

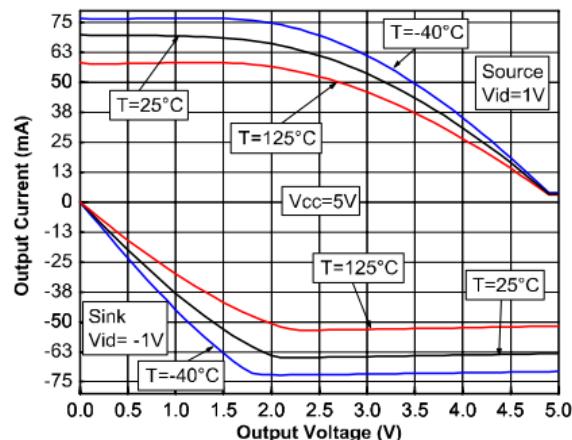


Figure 5: Voltage gain and phase vs. frequency at $V_{CC} = 1.5\text{ V}$

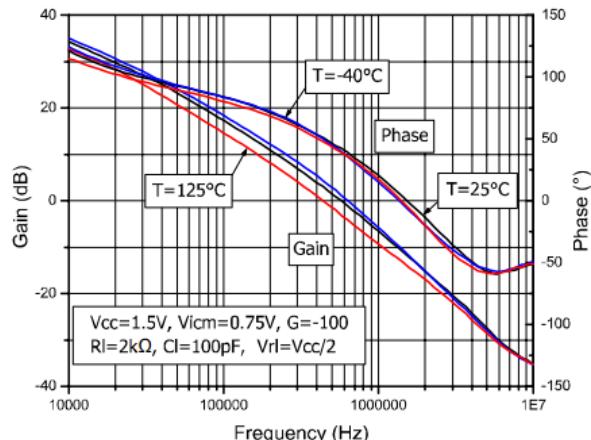


Figure 6: Voltage gain and phase vs. frequency at $V_{CC} = 5\text{ V}$

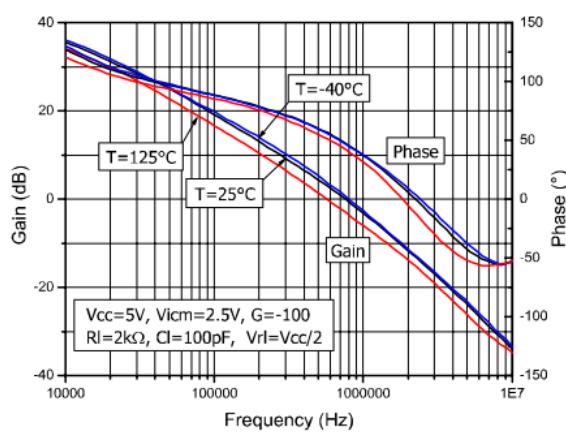
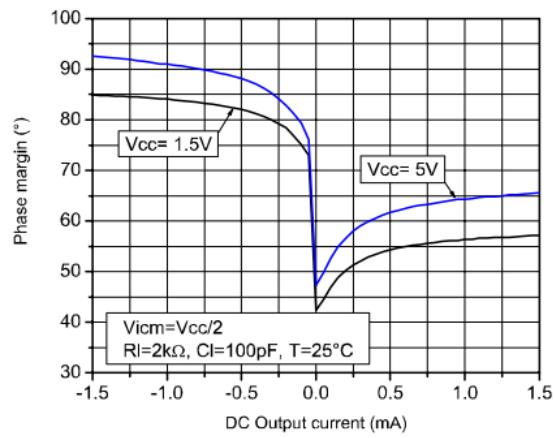


Figure 7: Phase margin vs. output current at $V_{CC} = 5\text{ V}$



Electrical characteristics

Figure 8: Positive slew rate vs. time

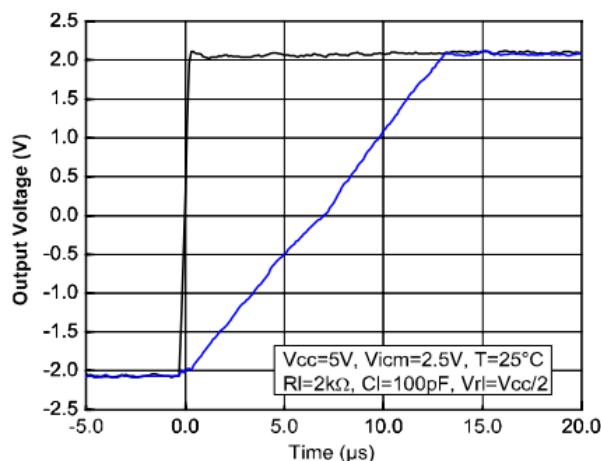


Figure 9: Negative slew rate vs. time

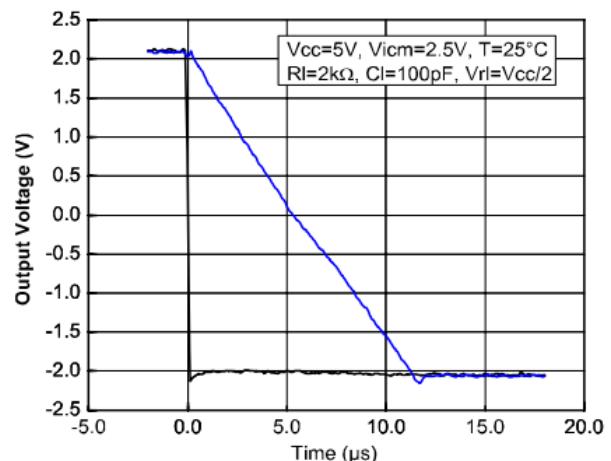


Figure 10: Positive slew rate vs. supply voltage

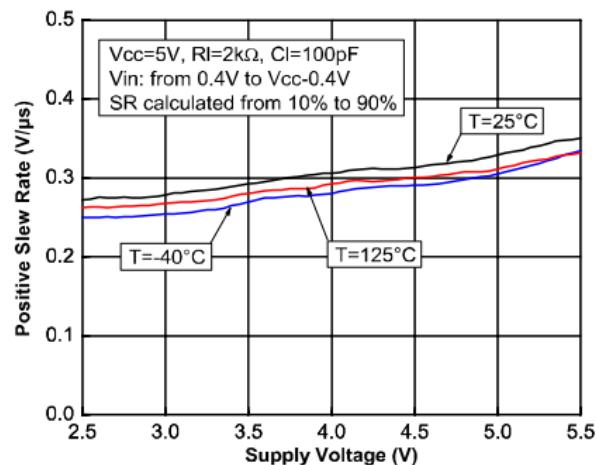


Figure 11: Negative slew rate vs. supply voltage

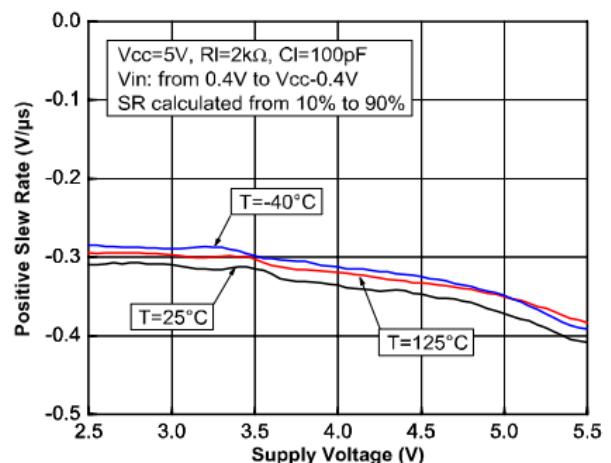


Figure 12: Distortion + noise vs. output voltage

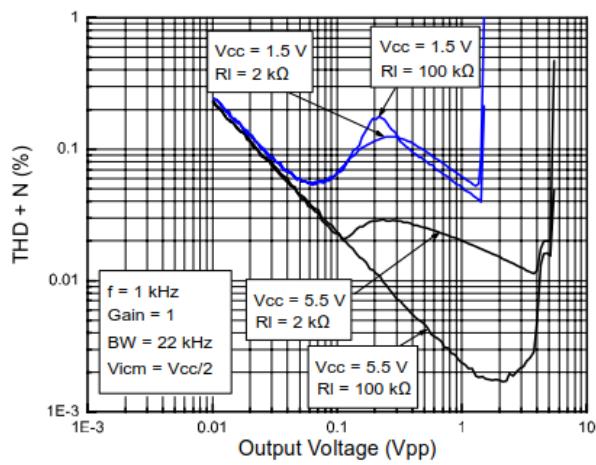


Figure 13: Distortion + noise vs. frequency

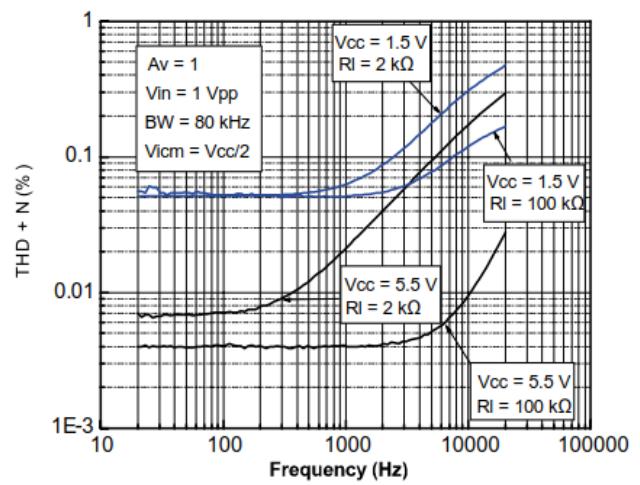


Figure 14: Noise vs. frequency

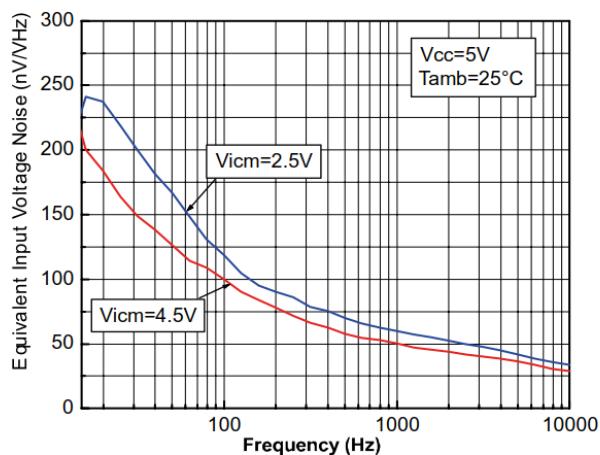
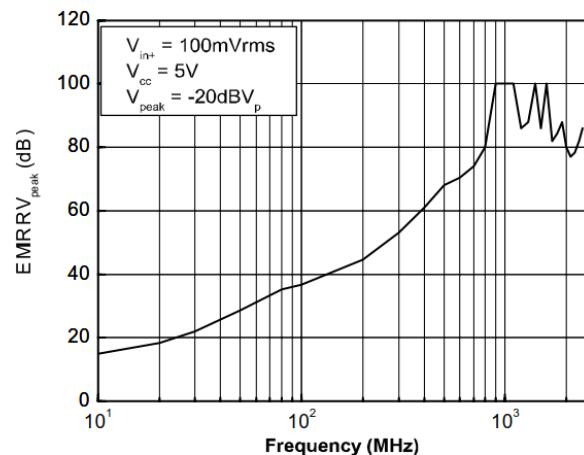
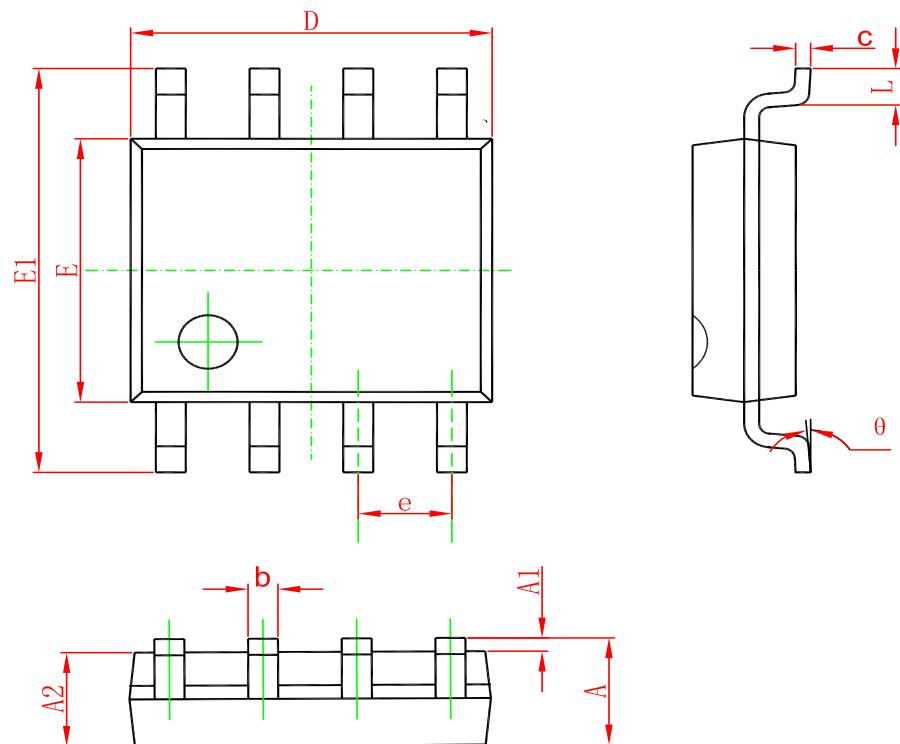


Figure 15: EMIRR vs. frequency at VCC = 5 V, T = 25 °C



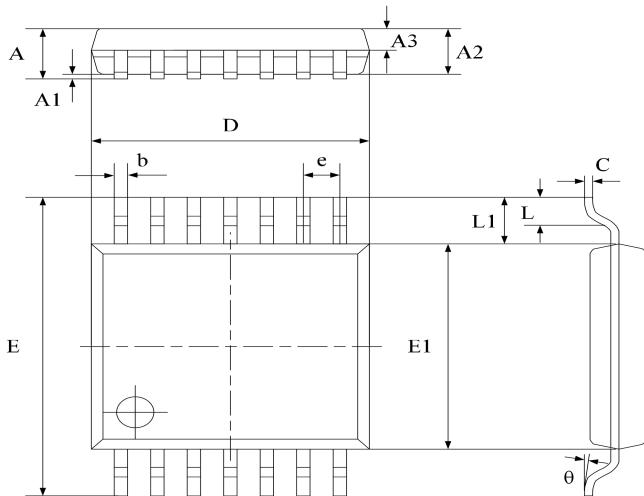
Package Dimension

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

TSSOP-14



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	-	1.200	-	0.0472
A1	0.050	0.150	0.002	0.006
A2	0.900	1.050	0.037	0.043
A3	0.390	0.490	0.016	0.020
b	0.200	0.290	0.008	0.012
C	0.130	0.180	0.005	0.007
D	4.860	5.060	0.198	0.207
E	6.200	6.600	0.253	0.269
E1	4.300	4.500	0.176	0.184
e	0.650 typ.		0.0256 typ.	
L1	1.000 ref.		0.0393 ref.	
L	0.450	0.750	0.018	0.031
θ	0°	8°	0°	8°

Ordering information

Order code	Package	Baseqty	Deliverymode	Marking
UMW TSV632IDT	SOP-8	2500	Tape and reel	TSV632
UMW TSV632AIDT	SOP-8	2500	Tape and reel	TSV632A
UMW TSV634IPT	TSSOP-14	4000	Tape and reel	TSV634